

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (currently amended) A method of manufacturing a semiconductor device comprising:

forming a resin layer on a semiconductor substrate in which a plurality of integrated circuits are formed;

~~forming a plurality of recesses in~~ making a surface of the resin layer uneven by forming a plurality of recesses therein;

forming an interconnecting line on the resin layer, the interconnecting line contacting the surface of the resin layer within an interior of ones of the plurality of ~~to pass along any one of the recesses along which the interconnecting line passes~~; and

cutting the semiconductor substrate into a plurality of semiconductor chips;

wherein each of the plurality of recesses is formed to have an opening width that is less than a thickness of the interconnecting line, and to have a depth of at least 1 μm .

2. (currently amended) The method of manufacturing a semiconductor device as defined in claim 1, wherein

~~wherein~~ the resin layer is formed of a photosensitive resin precursor,

~~wherein~~ in the step of forming the recesses, photolithography using a mask is applied, and

wherein the mask includes a transparent-and-opaque pattern for carrying out light irradiation with ~~too fine a~~ a pattern,

the pattern prevents ~~for~~ the photosensitive resin precursor from being completely to be resolved, and

the pattern prevents the recesses from penetrating an entire thickness of the resin layer.

3. (original) The method of manufacturing a semiconductor device as defined in claim 2,

wherein the photosensitive resin precursor is a negative type including an insoluble light-sensitive portion, and

wherein the transparent-and-opaque pattern includes an opaque portion having a width less than or equal to the thickness of the interconnecting line.

4. (original) The method of manufacturing a semiconductor device as defined in claim 3,

wherein the width of the opaque portion is less than or equal to one-fourths of a thickness of the resin layer.

5. (original) The method of manufacturing a semiconductor device as defined in claim 1, further comprising:

roughening the surface of the resin layer including inner surfaces of the recesses, after forming the recesses and before forming the interconnecting line.

6. (original) The method of manufacturing a semiconductor device as defined in claim 5, further comprising:

forming a second resin layer on the resin layer to cover at least a part of the interconnecting line, after forming the interconnecting line and before cutting the semiconductor substrate.

7. (original) The method of manufacturing a semiconductor device as defined in claim 6, further comprising:

forming recesses and projections on a surface of the second resin layer.

8. (original) The method of manufacturing a semiconductor device as defined in claim 7, further comprising:

forming a third resin layer on the second resin layer.

9. (original) The method of manufacturing a semiconductor device as defined in claim 8, further comprising:

forming recesses and projections on a surface of the third resin layer.

10. - 31. (cancelled)

32. (new) The method of manufacturing a semiconductor device as defined in claim 1, wherein the recesses form an interconnected lattice in plan view.

33. (new) The method of manufacturing a semiconductor device as defined in claim 1, wherein the recesses are disposed in an isolated manner in plan view.

34. (new) The method of manufacturing a semiconductor device as defined in claim 1, wherein the recesses include a group of concentric ring-shaped recesses in plan view.